		TENED TO COLUMN CO		Atty. Docket No.		Serial No.	
U.S. DEPARTMENT OF COMMERCE (7-80) PATENT AND TRADEMARK OFFICE LIST OF PRIOR ART CITED BY APPLICANT				BUR920010171US1 (15017)		09/683,328	
(U	se sev	veral sheets if necess	ary)				
JAN 0 4 2002			Applicant David M. Fried, et al. Filing Date December 14, 2001		Group Unassigned		
\		- <u>K</u> 3=)	U.S. P.	ATENT DOCUMENTS		SUBCLASS	FILING DATE
AMINE		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	(if appropriate)
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- / /		5,338,959	8/16/94	Kim, et al.		-	
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C. (1)	AF	6,031,269	2/29/00	Liu		-	
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Off?		Leland Chang, et al., "Gate Length Scaling and Threshold Voltage Control of Double-Gate MOSFET's Department of Electrical Engineering and Computer Sciences, University of California, 2000 IEEE. Keunwoo Kim, et al., "Optimal Double-Gate MOSFET's: Symmetrical or Asymmetrical Gates?, 19					
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EXAMIN	VER ,	1/1/10	1	citation is in conformance with MF	1/23/0)	f not in conformance